

N-channel TrenchMOS logic level FET 12 June 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. C	Quick reference data						
Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-		-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-		-	11	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-		-	36	W
Static chara	acteristics						
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-		97	125	mΩ
	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12	-		-	280	mΩ
		V_{GS} = 4.5 V; I _D = 5 A; T _j = 25 °C	-		-	155	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-		120	140	mΩ
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·	1				
Q _{GD}	gate-drain charge	V_{GS} = 5 V; I _D = 5 A; V _{DS} = 44 V; T _j = 25 °C; <u>Fig. 13</u>	-		2.6	-	nC

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N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	16	mJ

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	Drain		
3	S	source		G
mb	D	mounting base; connected to drain	DPAK (SOT428)	mbb076 S

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK92150-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				
BUK92150-55A/CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK92150-55A	9215055A
BUK92150-55A/CD	

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V

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N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DGR}	drain-gate voltage	R _{GS} 20 kΩ	-	55	V
V _{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	36	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2; Fig. 3</u>	-	11	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 3</u>	-	7.8	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 2	-	44	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	11	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	44	А
Avalanche r	ruggedness	, ,			
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	16	mJ

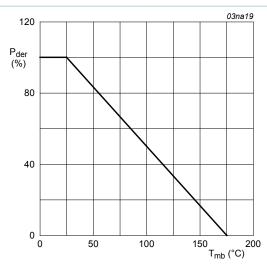
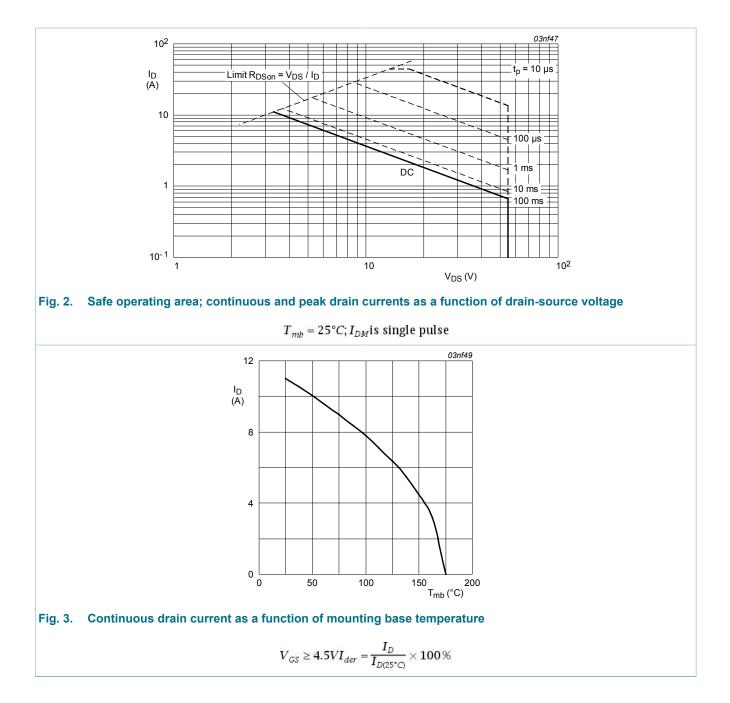


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

N-channel TrenchMOS logic level FET

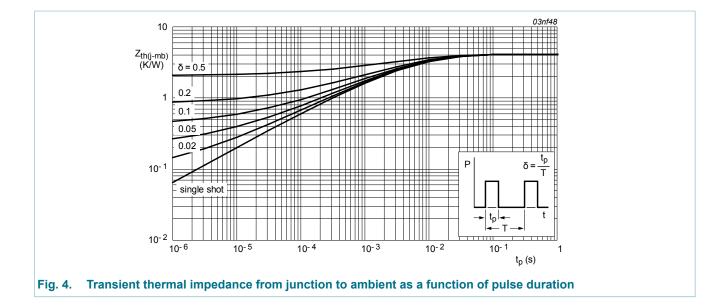


Thermal characteristics 9.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	-	4.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W

Product data sheet

N-channel TrenchMOS logic level FET

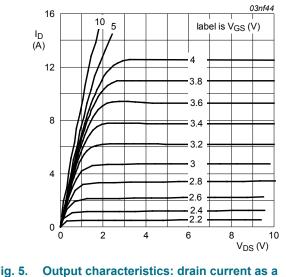


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	1				
V _{(BR)DSS} drain-source breakdown voltage		I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
V _{GS(th)} gate-source thresh voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS} drain leakage current	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS} gate leakage current	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-	97	125	mΩ
	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	280	mΩ
		V_{GS} = 4.5 V; I _D = 5 A; T _j = 25 °C	-	-	155	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11;</u> Fig. 12	-	120	140	mΩ

N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 44 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u>	-	6	-	nC
Q _{GS}	gate-source charge		-	0.76	-	nC
Q _{GD}	gate-drain charge		-	2.6	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 14</u>	-	240	338	pF
C _{oss}	output capacitance		-	50	65	pF
C _{rss}	reverse transfer capacitance		-	40	58	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R _L = 3.3 Ω; V _{GS} = 5 V; R _{G(ext)} = 10 Ω; T _j = 25 °C	-	8	-	ns
t _r	rise time		-	57	-	ns
t _{d(off)}	turn-off delay time		-	16	-	ns
t _f	fall time	_	-	13	-	ns
L _D	internal drain inductance	measured from drain to centre of die; T _j = 25 °C	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; $T_j = 25 \ ^{\circ}C$	-	7.5	-	nH
Source-dra	in diode					
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I_{S} = 20 A; d I_{S} /dt = -100 A/µs;	-	24	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C		26	-	nC







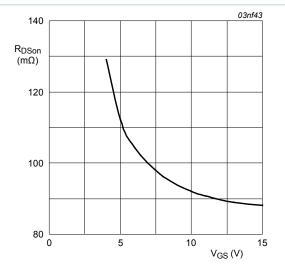


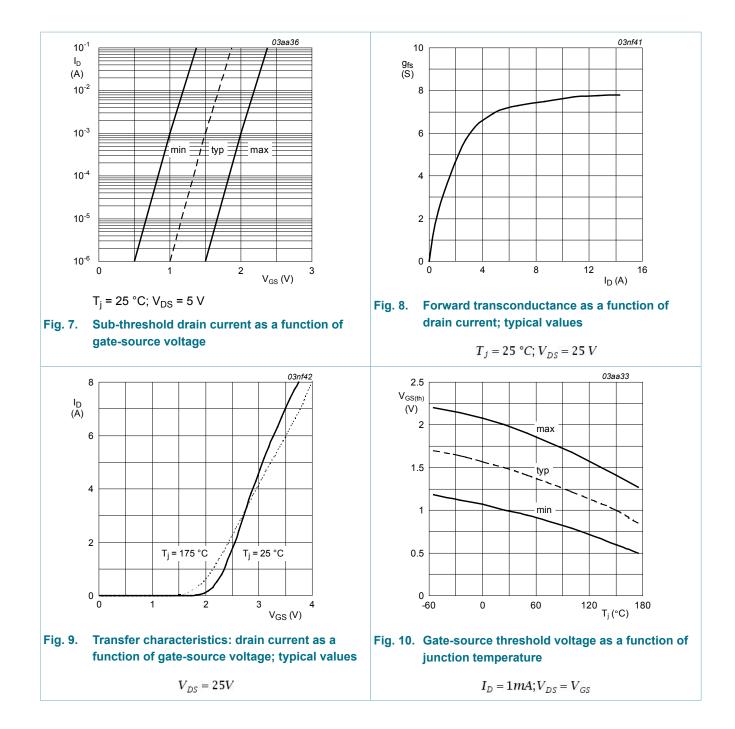
Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 5A$

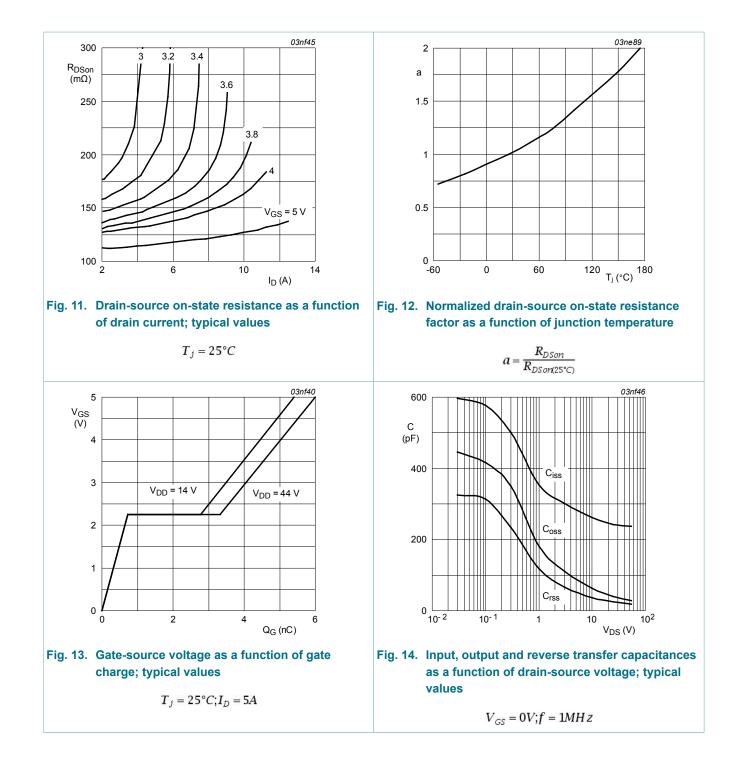
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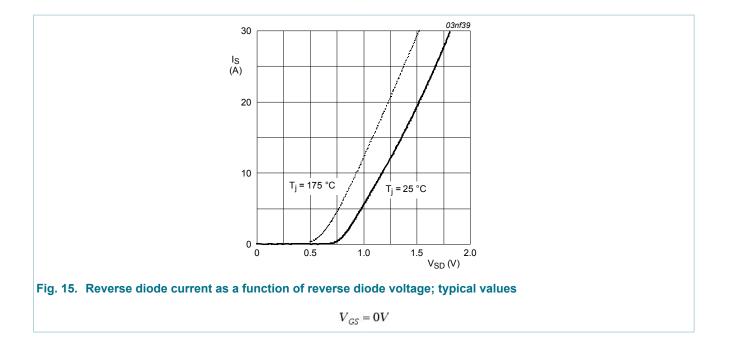
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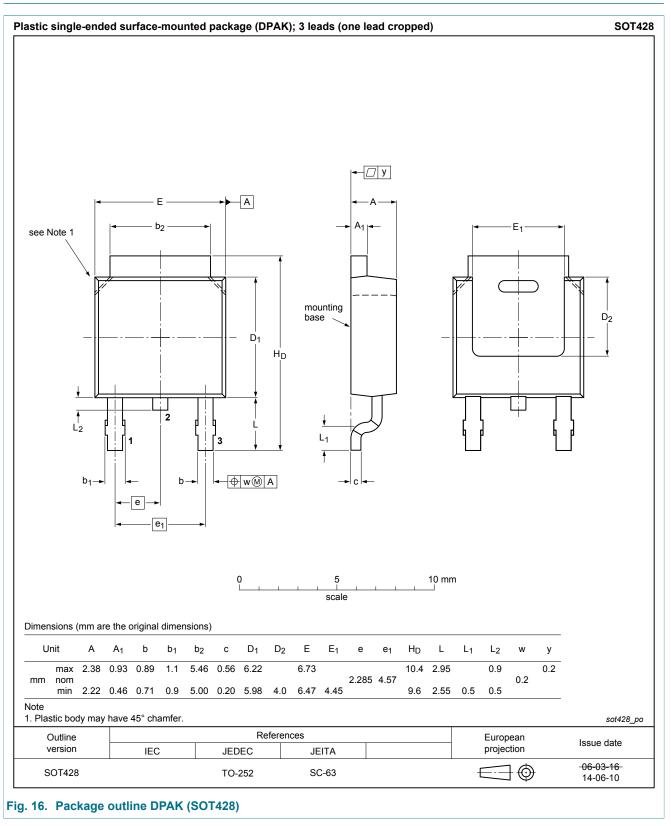
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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N-channel TrenchMOS logic level FET

13. Contents

General description1	
Features and benefits	
Applications1	
Quick reference data	
Pinning information2	2
Ordering information2	2
Marking2	
Limiting values2	2
Thermal characteristics4	ŀ
Characteristics5	5
Package outline 10)
Legal information11	
Data sheet status 11	
Definitions11	
Disclaimers11	
Trademarks 12	
	General description 1 Features and benefits 1 Applications 1 Quick reference data 1 Pinning information 2 Ordering information 2 Marking 2 Limiting values 2 Thermal characteristics 4 Characteristics 5 Package outline 10 Legal information 11 Data sheet status 11 Disclaimers 11 Trademarks 12

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